








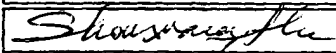
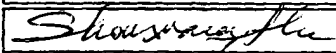
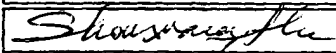


11/17/03

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention	High-Voltage Transistor With A Multi-Layer Conduction Region																								
<div>Application Number: 09/961229 </div> <div>Confirmation Number: 4375</div> <div>First Named Applicant: Vladimir Rumennik</div> <div>Attorney Docket Number: 03692.P007XD4</div> <div>Art Unit: 2811</div> <div>Examiner: Shouxiang Hu</div> <div>Search string: (6633065 or 6639277).pn.</div>																									
<div>RECEIVED NOV 28 2003 TECHNOLOGY CENTER 2800</div>																									
US Patent Documents																									
Note: Applicant is not required to submit a paper copy of cited US Patent Documents																									
<table border="1"><thead><tr><th>init</th><th>Cite.No.</th><th>Patent No.</th><th>Date</th><th>Patentee</th><th>Kind</th><th>Class</th><th>Subclass</th></tr></thead><tbody><tr><td></td><td>1</td><td>6633065</td><td>2003-10-14</td><td>Rumennik et al.</td><td>B2</td><td></td><td></td></tr><tr><td></td><td>2</td><td>6639277</td><td>2003-10-28</td><td>Rumennik et al.</td><td>B2</td><td></td><td></td></tr></tbody></table>		init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass		1	6633065	2003-10-14	Rumennik et al.	B2				2	6639277	2003-10-28	Rumennik et al.	B2		
init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass																		
	1	6633065	2003-10-14	Rumennik et al.	B2																				
	2	6639277	2003-10-28	Rumennik et al.	B2																				
Remarks																									
Note: Remarks are not for responding to an office action.																									
This information disclosure statement is being submitted concurrent with the filing of a Request for Continued Examination in the above-referenced application.																									
Signature																									
<table border="1"><tr><td>Examiner Name</td><td>Date</td></tr><tr><td></td><td>6/28/04</td></tr></table>		Examiner Name	Date		6/28/04																				
Examiner Name	Date																								
	6/28/04																								



#15 / E/e/m/c
105
11/40-03
R/bh

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18
Stylesheet Version v18.0

Title of Invention	High-Voltage Transistor With Multi-Layered Conduction Region																								
Application Number: 09/961229 Confirmation Number: 4375 First Named Applicant: Vladimir Rumennik Attorney Docket Number: 03692.P007XD4 Art Unit: 2811 Examiner: Shouxiang Hu. Search string: (4614959 or 5294824).pn.																									
US Patent Documents Note: Applicant is not required to submit a paper copy of cited US Patent Documents																									
<table border="1"><thead><tr><th>Init</th><th>Cite.No.</th><th>Patent No.</th><th>Date</th><th>Patentee</th><th>Kind</th><th>Class</th><th>Subclass</th></tr></thead><tbody><tr><td>EX</td><td>1</td><td>4614959</td><td>1986-09-01</td><td>Nakagawa</td><td></td><td></td><td></td></tr><tr><td>EX</td><td>2</td><td>5294824</td><td>1994-03-01</td><td>Okada</td><td></td><td></td><td></td></tr></tbody></table>		Init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass	EX	1	4614959	1986-09-01	Nakagawa				EX	2	5294824	1994-03-01	Okada			
Init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass																		
EX	1	4614959	1986-09-01	Nakagawa																					
EX	2	5294824	1994-03-01	Okada																					
Signature <table border="1"><thead><tr><th>Examiner Name</th><th>Date</th></tr></thead><tbody><tr><td><i>Shouxiang Hu</i></td><td>6/23/04</td></tr></tbody></table>		Examiner Name	Date	<i>Shouxiang Hu</i>	6/23/04																				
Examiner Name	Date																								
<i>Shouxiang Hu</i>	6/23/04																								

09961229 - IDS Page 3 of 4 (06-19-2003)